

# XP2322GN-HF

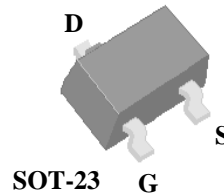
**Halogen-Free Product**

*N-CHANNEL ENHANCEMENT MODE*

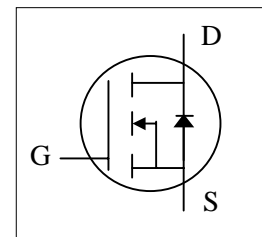
*POWER MOSFET*



- ▼ Capable of 1.8V Gate Drive
- ▼ Simple Drive Requirement
- ▼ Surface Mount Package
- ▼ RoHS Compliant & Halogen-Free



$BV_{DSS}$	20V
$R_{DS(ON)}$	90m $\Omega$
$I_D$	2.5A



## Description

XP2322 series are innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The special design SOT-23 package with good thermal performance is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for voltage conversion or switch applications.

## Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 8$	V
$I_D@T_A=25^\circ\text{C}$	Drain Current <sup>3</sup> , $V_{GS}$ @ 4.5V	2.5	A
$I_D@T_A=70^\circ\text{C}$	Drain Current <sup>3</sup> , $V_{GS}$ @ 4.5V	2.0	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	10	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	0.833	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	150	$^\circ\text{C}/\text{W}$

**Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.6A	-	-	90	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =1A	-	-	120	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.3A	-	-	150	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =1mA	0.25	-	1	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =2A	-	2	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =2.2A	-	7	11	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =16V	-	0.7	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	2.5	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =10V	-	6	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =1A	-	12	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	16	-	ns
t <sub>f</sub>	Fall Time	V <sub>GS</sub> =5V	-	4	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	350	560	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =20V	-	55	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	48	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	3.2	-	Ω

**Source-Drain Diode**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =0.7A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =2A, V <sub>GS</sub> =0V,	-	20	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	di/dt=100A/μs	-	13	-	nC

**Notes:**

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board , t ≤10sec ; 360 °C/W when mounted on Min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

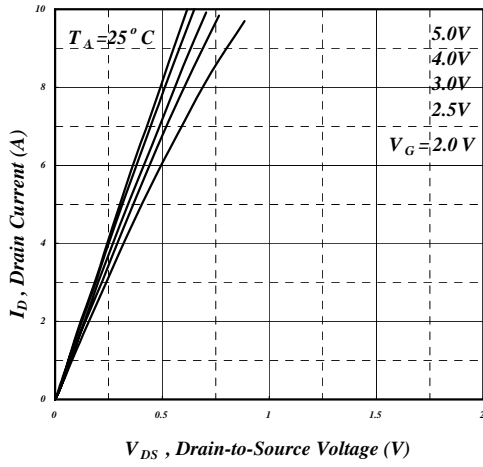
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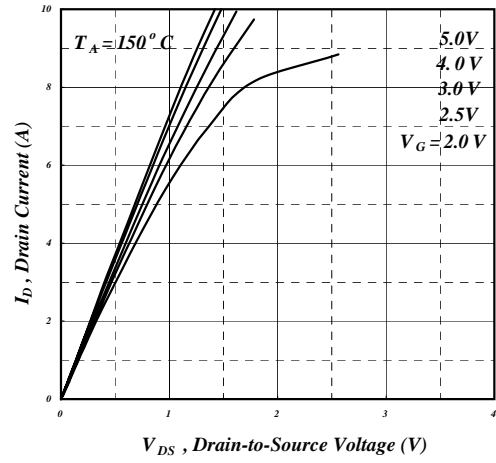
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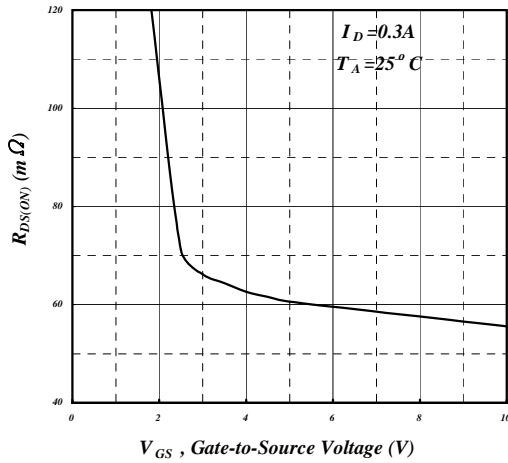
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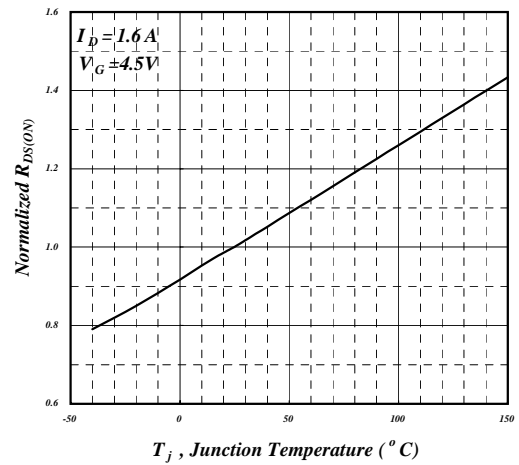
**Fig 1. Typical Output Characteristics**



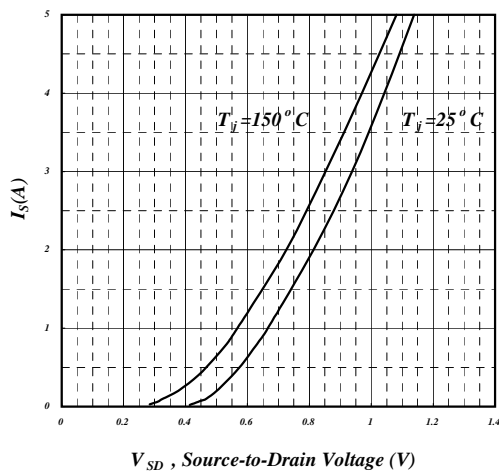
**Fig 2. Typical Output Characteristics**



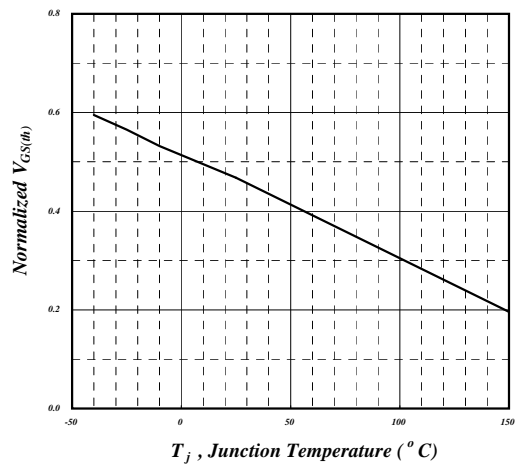
**Fig 3. On-Resistance v.s. Gate Voltage**



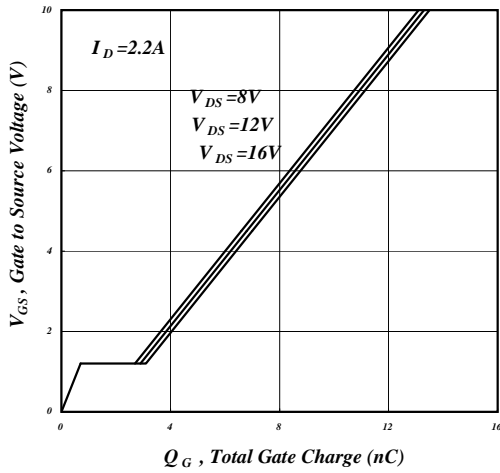
**Fig 4. Normalized On-Resistance v.s. Junction Temperature**



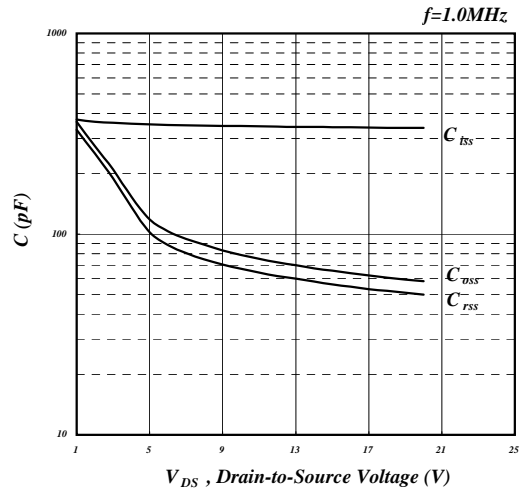
**Fig 5. Forward Characteristic of Reverse Diode**



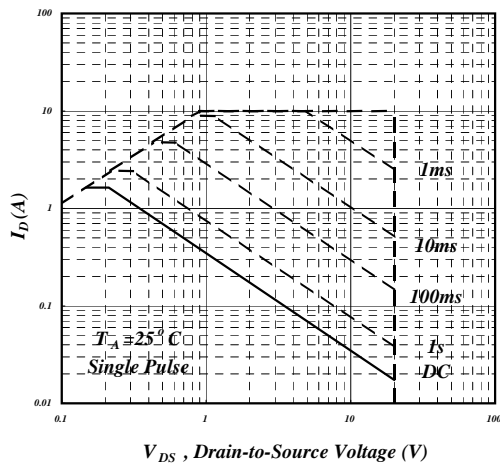
**Fig 6. Gate Threshold Voltage v.s. Junction Temperature**



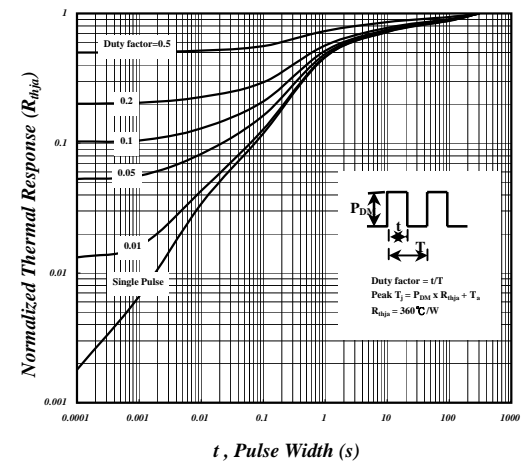
**Fig 7. Gate Charge Characteristics**



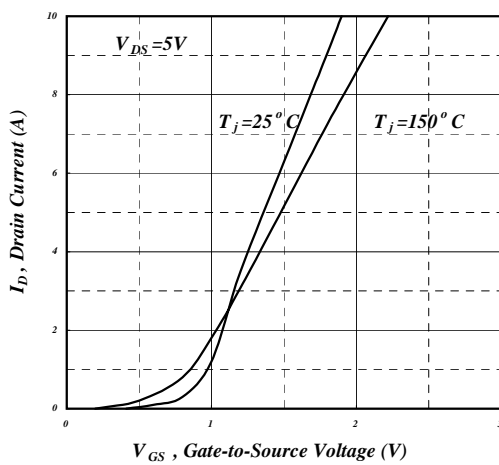
**Fig 8. Typical Capacitance Characteristics**



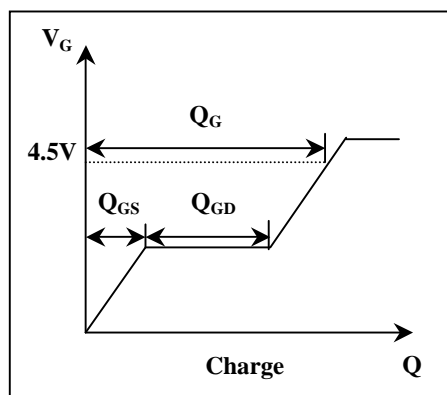
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Transfer Characteristics**



**Fig 12. Gate Charge Circuit**